

This listing of claims will replace all prior versions and listings of claims in the application:

Listing of Claims:

Claim 1. (original) A trenched field effect transistor comprising:
a semiconductor substrate;
a trench extending a predetermined depth into said semiconductor substrate;
a pair of doped source junctions, positioned on opposite sides of the trench;
a doped heavy body positioned adjacent each source junction on the opposite side
of the source junction from the trench, the deepest portion of said heavy body extending less
deeply into said semiconductor substrate than said predetermined depth of said trench; and
a doped well surrounding the heavy body beneath the heavy body.

Claims 2-45 (cancelled)